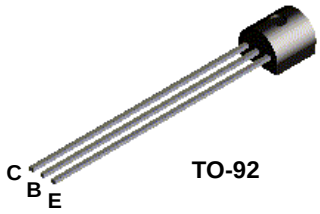
FAIRCHILD
SEMICONDUCTOR TM

2N3903



TO-92

NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3903	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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NPN General Purpose Amplifier
(continued)

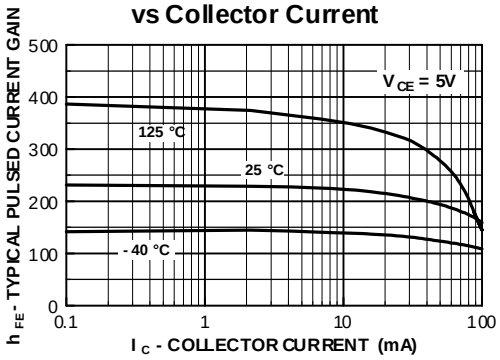
Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	I_C = 1.0 mA, I_B = 0	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 µA, I_C = 0	6.0		V
I_{CEX}	Collector Cutoff Current	V_{CE} = 30 V, V_{OB} = 3.0 V		50	nA
I_{BL}	Base Cutoff Current	V_{CE} = 30 V, V_{OB} = 3.0 V		50	nA
ON CHARACTERISTICS*					
h_{FE}	DC Current Gain	V_{CE} = 1.0 V, I_C = 0.1 mA V_{CE} = 1.0 V, I_C = 1.0 mA V_{CE} = 1.0 V, I_C = 10 mA V_{CE} = 1.0 V, I_C = 50 mA V_{CE} = 1.0 V, I_C = 100 mA	20 35 50 30 15	 150 	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 50 mA, I_B = 5.0 mA		0.2 0.3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 10 mA, I_B = 1.0 mA I_C = 50 mA, I_B = 5.0 mA	0.65	0.85 0.95	V V
SMALL SIGNAL CHARACTERISTICS					
C_{ob}	Output Capacitance	V_{CB} = 5.0 V, f = 100 kHz		4.0	pF
C_{ib}	Input Capacitance	V_{EB} = 0.5 V, f = 100 kHz		8.0	pF
h_{fe}	Small-Signal Current Gain	I_C = 10 mA, V_{CE} = 20 V, f = 100 MHz	2.5		
h_{fe}	Small-Signal Current Gain	V_{CE} = 10 V, I_C = 1.0 mA	50	200	
h_{ie}	Input Impedance	f = 1.0 kHz	1.0	8.0	kΩ
h_{re}	Voltage Feedback Ratio		0.1	5.0	x 10^{-4}
h_{oe}	Output Admittance		1.0	40	µmhos
NF	Noise Figure	V_{CE} = 5.0 V, I_C = 100 µA, R_S = 1.0 kΩ, B_W = 10 Hz to 15.7 kHz		6.0	dB
SWITCHING CHARACTERISTICS					
t_d	Delay Time	V_{CC} = 3.0 V, I_C = 10 mA,		35	ns
t_r	Rise Time	I_{B1} = 1.0 mA , $V_{ob\ (off)}$ = 0.5 V		35	ns
t_s	Storage Time	V_{CC} = 3.0 V, I_C = 10 mA		175	ns
t_f	Fall Time	I_{B1} = I_{B2} = 1.0 mA		50	ns

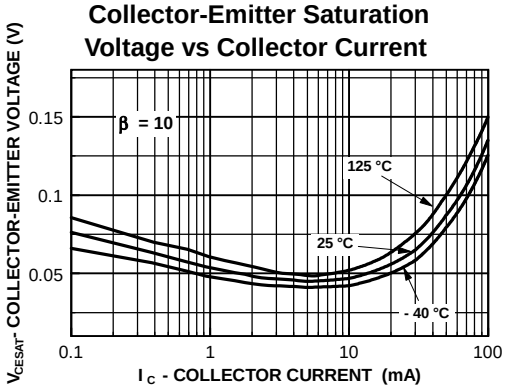
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

Typical Characteristics

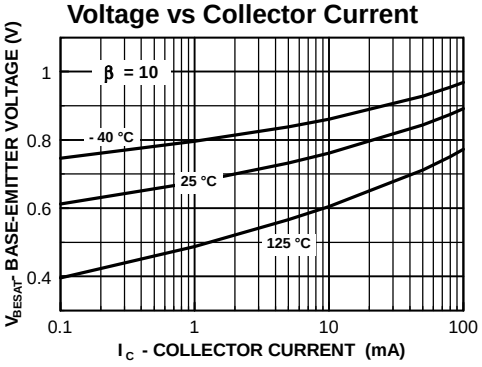
Typical Pulsed Current Gain vs Collector Current



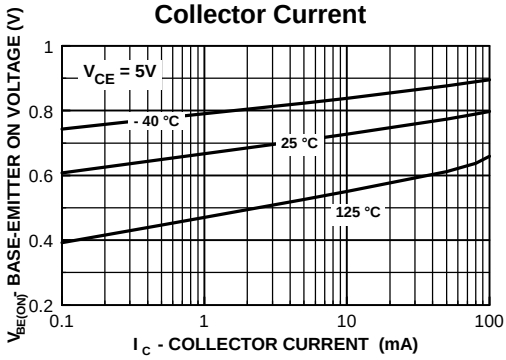
Collector-Emitter Saturation Voltage vs Collector Current



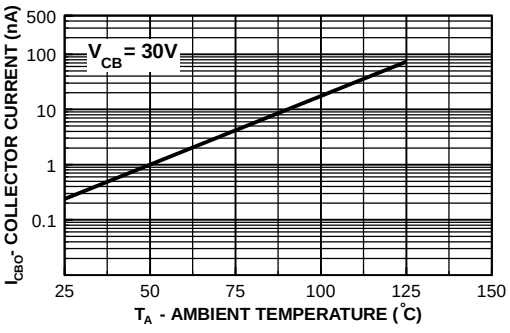
Base-Emitter Saturation Voltage vs Collector Current



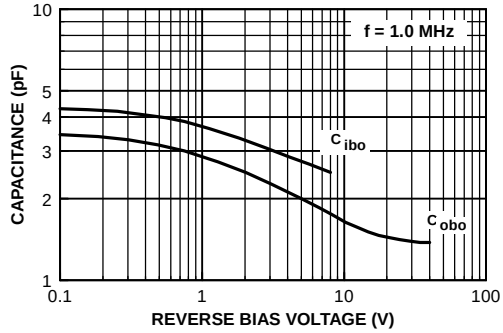
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

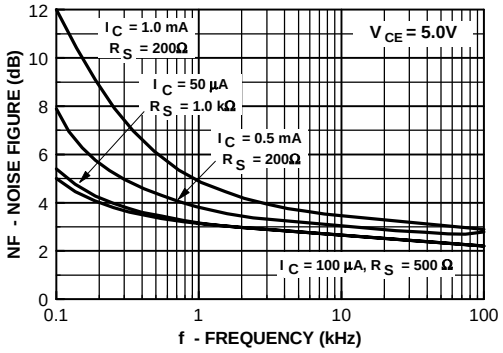


Capacitance vs Reverse Bias Voltage

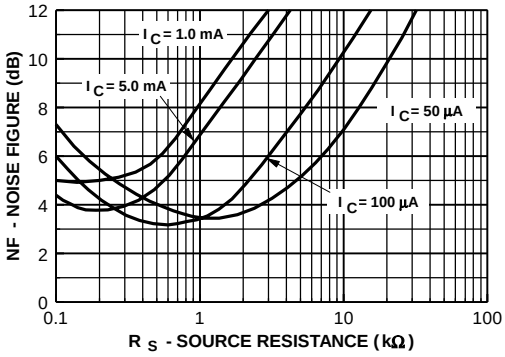


Typical Characteristics (continued)

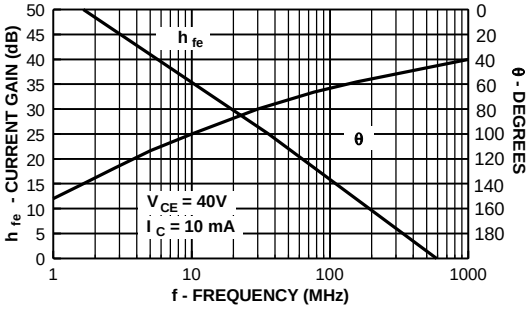
Noise Figure vs Frequency



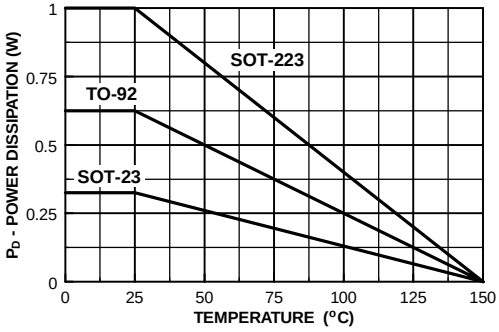
Noise Figure vs Source Resistance



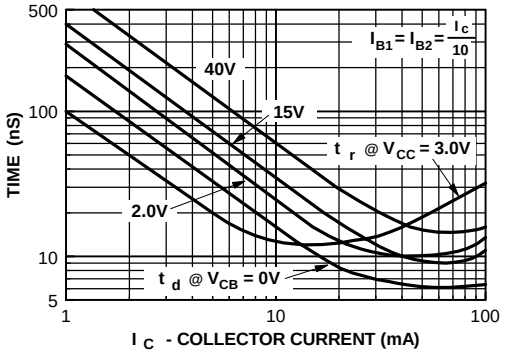
Current Gain and Phase Angle vs Frequency



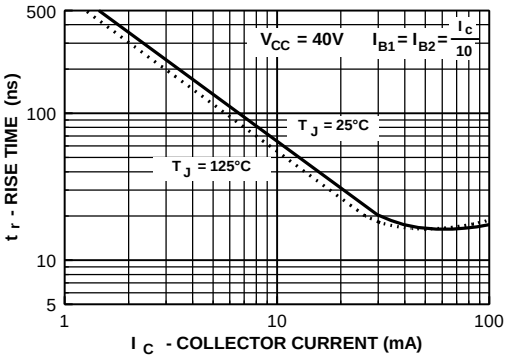
Power Dissipation vs Ambient Temperature



Turn-On Time vs Collector Current

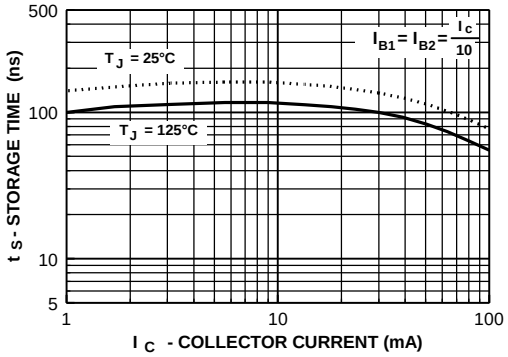


Rise Time vs Collector Current

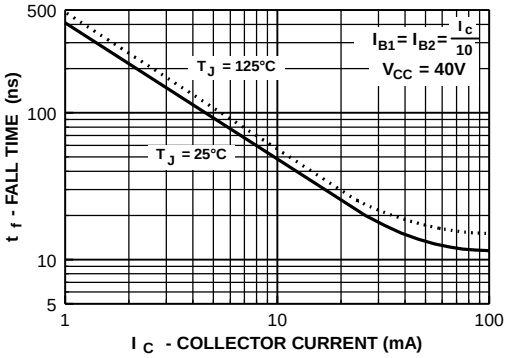


Typical Characteristics (continued)

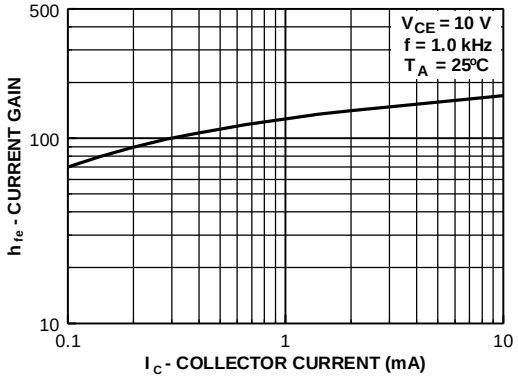
Storage Time vs Collector Current



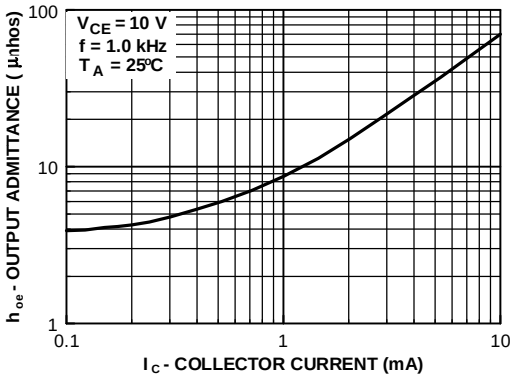
Fall Time vs Collector Current



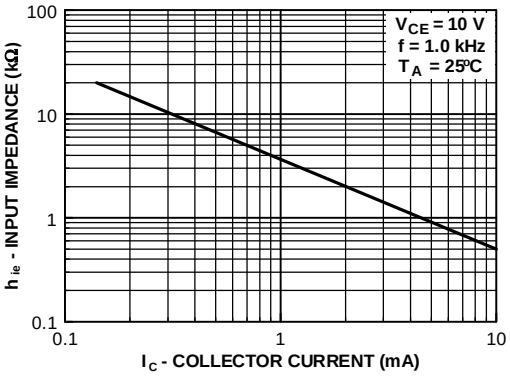
Current Gain



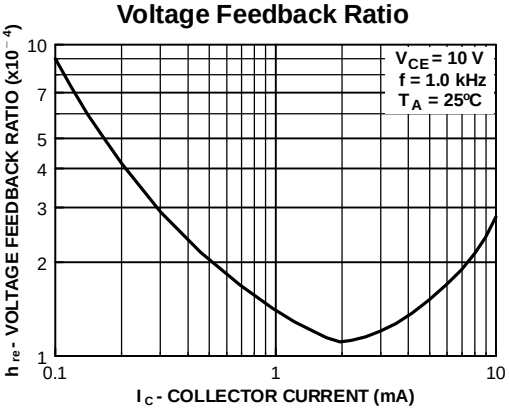
Output Admittance



Input Impedance



Voltage Feedback Ratio



Test Circuits

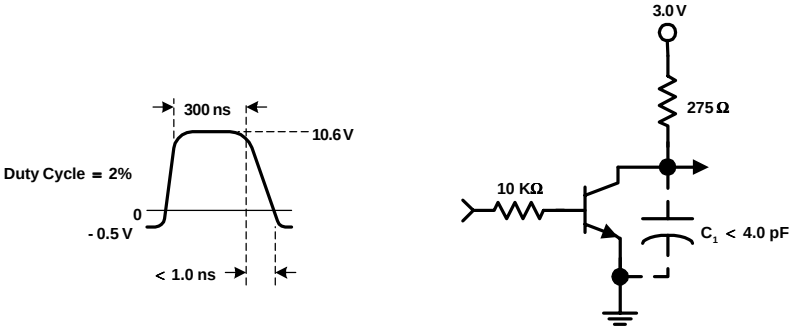


FIGURE 1: Delay and Rise Time Equivalent Test Circuit

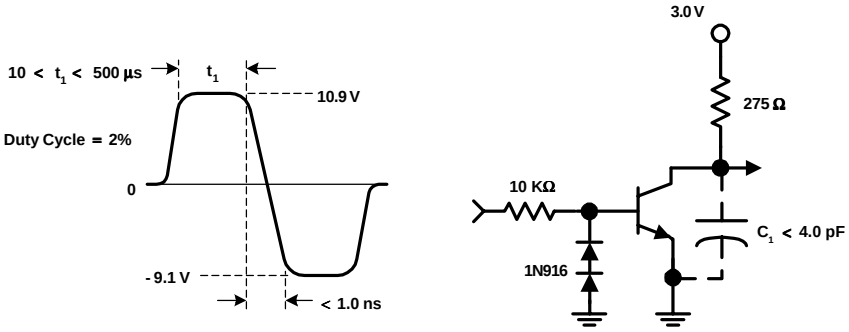


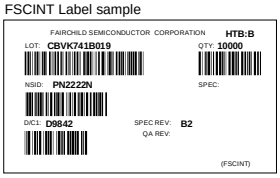
FIGURE 2: Storage and Fall Time Equivalent Test Circuit

TO-92 Tape and Reel Data

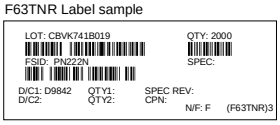
FAIRCHILD SEMICONDUCTOR TM

TO-92 Packaging Configuration: Figure 1.0

FSCINT Label sample

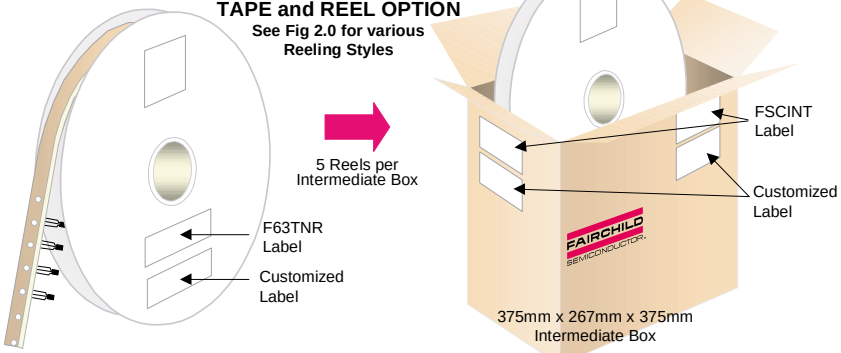


F63TNR Label sample



TAPE and REEL OPTION

See Fig 2.0 for various Reeling Styles



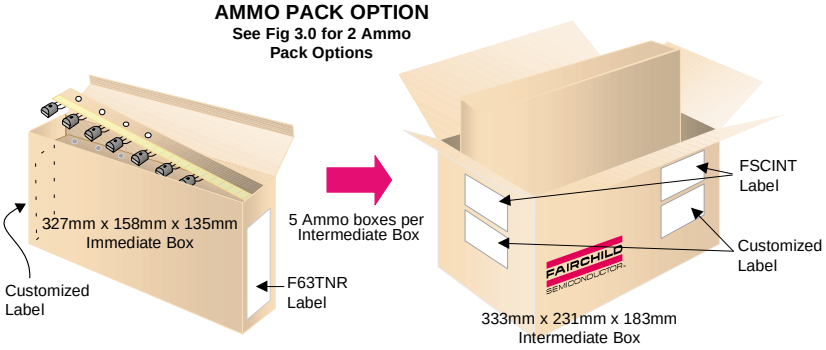
TO-92 TNR/AMMO PACKING INFROMATION

Packing	Style	Quantity	EOL code
Reel	A	2,000	D26Z
	E	2,000	D27Z
Ammo	M	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.22 gm
Reel weight with components = 1.04 kg
Ammo weight with components = 1.02 kg
Max quantity per intermediate box = 10,000 units

AMMO PACK OPTION

See Fig 3.0 for 2 Ammo Pack Options

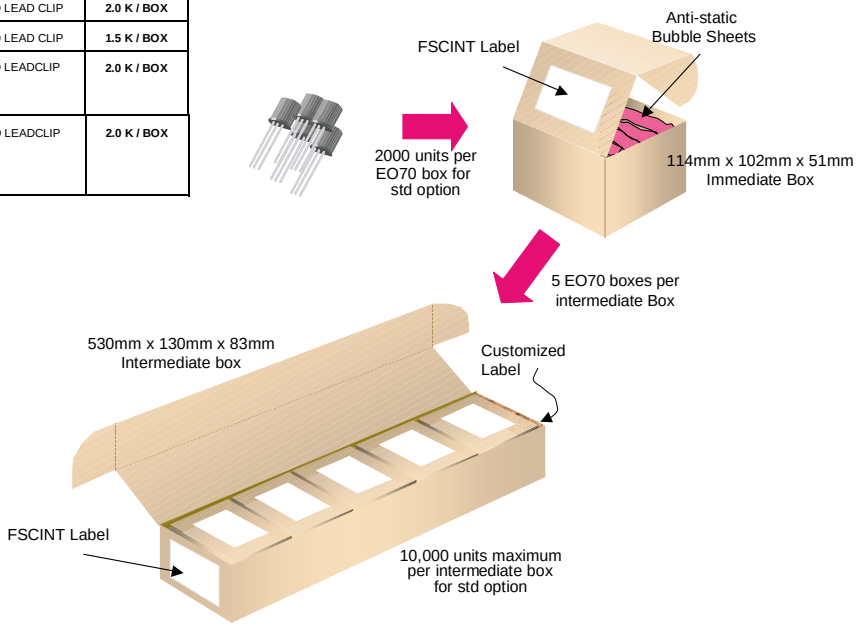


(TO-92) BULK PACKING INFORMATION

EOL CODE	DESCRIPTION	LEADCLIP DIMENSION	QUANTITY
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0 K / BOX
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5 K / BOX
NO EOL CODE	TO-92 STANDARD STRAIGHT FOR: PKG 92, 94 (NON PROELECTRON SERIES), 96	NO LEADCLIP	2.0 K / BOX
L34Z	TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98	NO LEADCLIP	2.0 K / BOX

BULK OPTION

See Bulk Packing Information table



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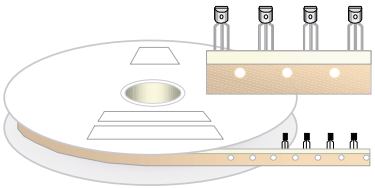
TO-92 Tape and Reel Data, continued

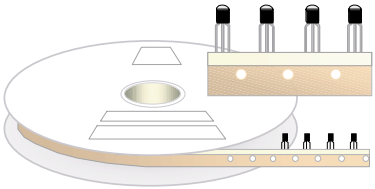
TO-92 Reeling Style
Configuration: Figure 2.0

Machine Option “A” (H)



Style “A”, D26Z, D70Z (s/h)

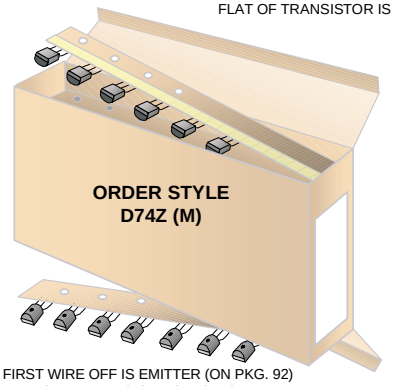
Machine Option “E” (J)



Style “E”, D27Z, D71Z (s/h)

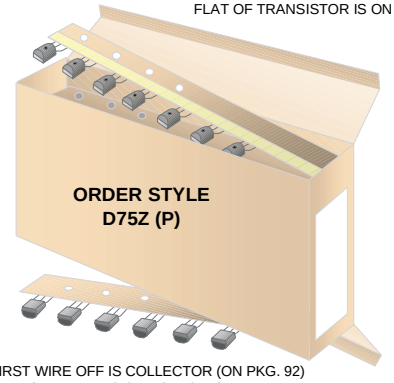
TO-92 Radial Ammo Packaging
Configuration: Figure 3.0

FIRST WIRE OFF IS COLLECTOR
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON TOP



FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

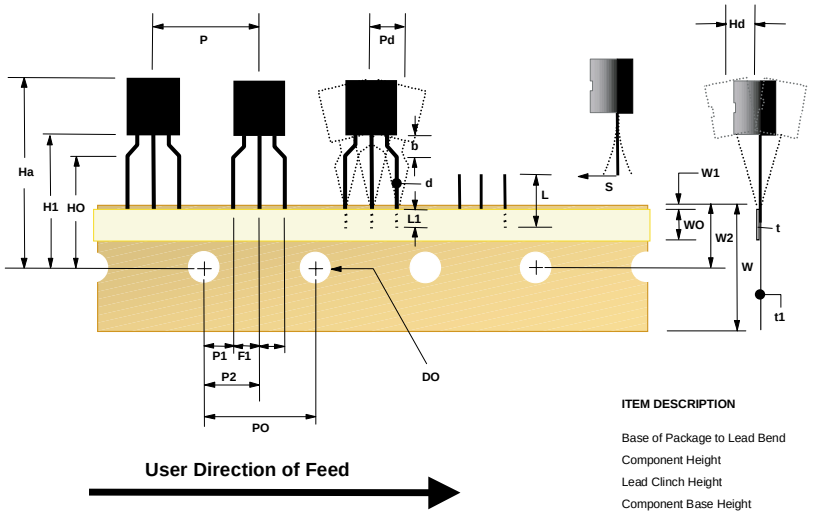
FIRST WIRE OFF IS EMITTER
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR (ON PKG. 92)
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON TOP

TO-92 Tape and Reel Data, continued

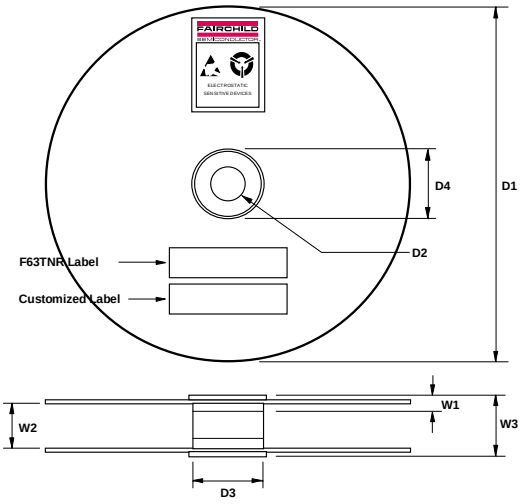
TO-92 Tape and Reel Taping
Dimension Configuration: Figure 4.0



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.928 (+/- 0.025)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment (side/side)	Pd	0.040 (max)
Component Alignment (front/back)	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0 .010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

Note : All dimensions are in inches.

TO-92 Reel
Configuration: Figure 5.0



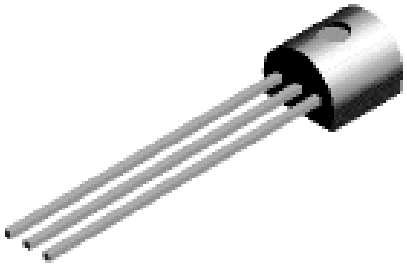
ITEM DESCRIPTION	SYSMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13.975	14.025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Flange to Flange Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

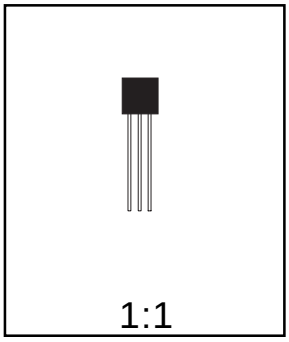
Note: All dimensions are inches

TO-92 Package Dimensions

FAIRCHILD SEMICONDUCTOR™

TO-92 (FS PKG Code 92, 94, 96)





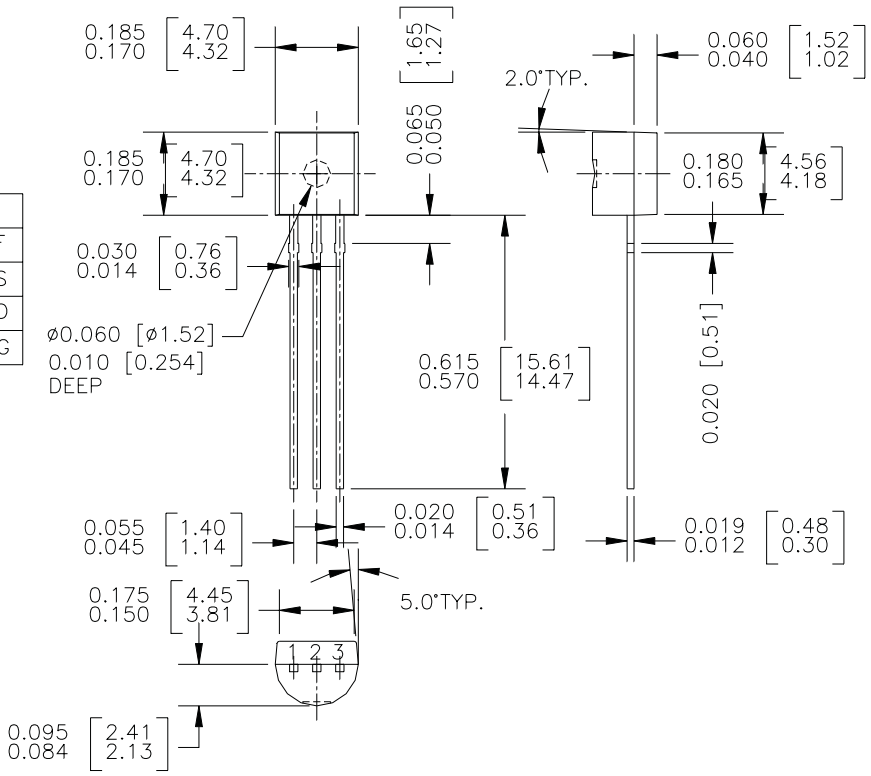
Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

TO−92 (92,94,96)

PIN	92		94		96	
	B	F	B	F	B	F
1	E	D	E	D	B	S
2	B	S	C	G	E	D
3	C	G	B	S	C	G



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FACT™
FACT Quiet Series™
FAST®
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GlobalOptoisolator™
GTO™
HiSeC™
ISOPLANAR™
MICROWIRE™
OPTOLOGIC™
OPTOPLANAR™
PACMAN™
POP™
PowerTrench®
QFET™
QS™
QT Optoelectronics™
Quiet Series™
SILENT SWITCHER®
SMART START™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SyncFET™
TinyLogic™
UHC™
VCX™

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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